

MG15N6ES1 Transistors

Three-Phase Bridge IGBT Power Module

Isolated Case (Y/N) Yes

Circuits Per Package 1

$V_{(BR)CES}$ (V) 1.0k

$V_{(BR)GES}$ (V)

$I_{(C)}$ Max. (A) 15

Absolute Max. Power Diss. (W) 125

Minimum Operating Temp (\varnothing C)

Maximum Operating Temp (\varnothing C)

Thermal Resistance Junc-Case

$I_{(CES)}$ Min. (A)

@ $V_{(CES)}$ (V) (Test Condition)

$I_{(GES)}$ Max. (A)

@ $V_{(GES)}$ (V) (Test Condition)

$V_{(CE)sat}$ Max. (V) 5.0

@ $I_{(C)}$ (A) (Test Condition)

@ $V_{(GE)}$ (Test Condition)

$V_{(GE)th}$ Max. (V)

@ $I_{(C)}$ (A) (Test Condition)

@ $V_{(CE)}$ (V) (Test Condition)

$g_{(fe)}$ Min. (S) Trans. admitt.

$q_{(fe)}$ Max. (S) Trans. admitt.